N-Channel 20-V (D-S) MOSFET

| PRODUCT SUMMARY | | | | | | |
|--------------------------|--|---------------------------------|-----------------------|--|--|--|
| V _{(BR)DSS} (V) | $r_{DS(on)}$ (Ω) | I _D (A) ^c | Q _g (Typ.) | | | |
| 20 | 0.0025 at V_{GS} = 4.5 V | 76 | 27 nC | | | |
| | 0.0031 at V _{GS} = 2.5 V | 47 | 27 110 | | | |

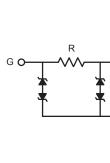
FEATURES

- DT-Trench Power MOSFET
- 175 °C Junction Temperature
- 100 % R_g Tested
- · 100 % UIS Tested
- · Typical ESD Protection 4000 V



TO-252





APPLICATIONS

OR-ing

| Parameter | Symbol | Limit | Unit | | |
|---|-------------------------------------|-----------------|------------------|----|--|
| Drain-Source Voltage | V _{DS} | 20 | V | | |
| Gate-Source Voltage | V _{GS} | ± 12 | V | | |
| Continuous Drain Current (T _{.I} = 175 °C) | T _C = 25 °C | | 76 ^a | A | |
| Continuous Diain Current (1) = 173 C) | T _C = 100 °C | l _D | 47 ^a | | |
| Pulsed Drain Current | I _{DM} | 290 | Α . | | |
| Single Pulse Avalanche Current | e Pulse Avalanche Current | | 62 | | |
| Single Pulse Avalanche Energy | L = 0.1 IIII | E _{AS} | 99 | mJ | |
| Mariana Barra Birain atianh | T _C = 25 °C | В | 127 ^c | W | |
| Maximum Power Dissipation ^b | T _A = 25 °C ^d | $ P_D$ | 3.96 | | |
| Operating Junction and Storage Temperature Ra | T _J , T _{stg} | - 55 to 175 | °C | | |

| THERMAL RESISTANCE RATINGS | | | | | | |
|---|--------------|-------------------|------|------|------|--|
| Parameter | | Symbol | Тур. | Max. | Unit | |
| Maximum Junction-to-Ambient ^{b, d} | t ≤ 10 sec | R _{thJA} | 32 | 40 | °C/W | |
| Maximum Junction-to-Case | Steady State | R _{thJC} | 1.02 | 2 | C/VV | |

Notes:

- a. Package limited.

- b. Duty cycle ≤ 1 %.
 c. See SOA curve for voltage derating.
 d. When mounted on 1" square PCB (FR-4 material).



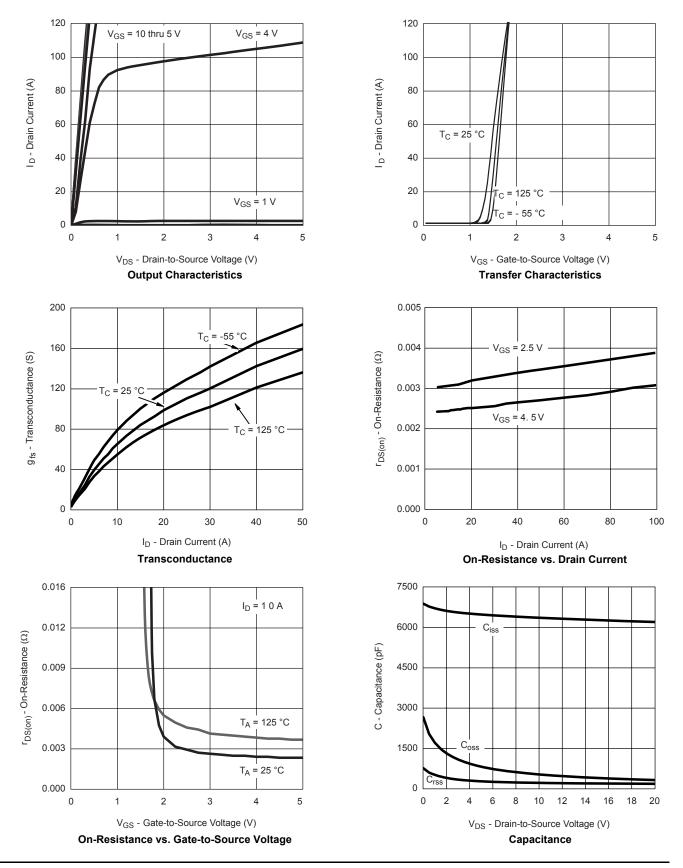
| Parameter | Symbol | Test Conditions | Min. | Тур. | Max. | Unit | |
|---|----------------------|---|------|---------------|--------------|------|--|
| Static | | | | | | | |
| Drain-Source Breakdown Voltage | V _{(BR)DSS} | $V_{DS} = 0 \text{ V}, I_{D} = 250 \mu\text{A}$ | 20 | | | V | |
| Gate-Threshold Voltage | V _{GS(th)} | $V_{DS} = V_{GS}, I_{D} = 250 \mu A$ | 0.5 | | 1.0 | | |
| Gate-Body Leakage | I _{GSS} | $V_{DS} = 0 V, V_{GS} = \pm 12 V$ | | | ± 10 | uA | |
| | | V _{DS} = 20 V, V _{GS} = 0 V | | | 1 | μA | |
| Zero Gate Voltage Drain Current | I _{DSS} | V _{DS} = 16 V, V _{GS} = 0 V, T _J = 125 °C | | | 50 | | |
| | | V _{DS} = 16V, V _{GS} = 0 V, T _J = 175 °C | | | 250 | 1 | |
| On-State Drain Current ^a | I _{D(on)} | $V_{DS} \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$ | 120 | | | Α | |
| | | $V_{GS} = 4.5 \text{ V}, I_D = 20 \text{ A}$ | | 0.0025 0.0031 | | | |
| | | V _{GS} = 4.5 V, I _D = 10 A, T _J = 125 °C | | | 0.0037 | | |
| Drain-Source On-State Resistance ^a | r _{DS(on)} | V _{GS} = 4.5 V, I _D = 10 A, T _J = 175 °C | | | 0.0042 | Ω | |
| | | $V_{GS} = 2.5 \text{ V}, I_D = 15 \text{ A}$ | | 0.0031 | 0.0038 | | |
| Forward Transconductance ^a | 9 _{fs} | V _{DS} = 10 V, I _D = 20 A | | 98 | | S | |
| Dynamic ^b | • | | | | ' | | |
| Input Capacitance | C _{iss} | | | 6250 | | pF | |
| Output Capacitance | C _{oss} | V_{GS} = 0 V, V_{DS} = 10 V, f = 1 MHz | | 495 | | | |
| Reverse Transfer Capacitance | C _{rss} | | | 205 | | | |
| Total Gate Charge ^b | Qg | | | 27 | 50 | | |
| Gate-Source Charge ^b | Q _{gs} | $V_{DS} = 10 \text{ V}, V_{GS} = 4.5 \text{ V}, I_{D} = 50 \text{ A}$ | | 6.5 | | nC | |
| Gate-Drain Charge ^b | Q _{gd} | | | 7 | | | |
| Gate Resistance | R _g | | 0.82 | 1.6 | 2.8 | Ω | |
| Turn-On Delay Time ^b | t _{d(on)} | | | 15 | 29 | | |
| Rise Time ^b | t _r | V_{DD} = 10 V, R_L = 0.2 Ω | | 7 | 17 | | |
| Turn-Off Delay Time ^b | t _{d(off)} | $I_D \cong 50 \text{ A}, V_{GEN} = 4.5 \text{ V}, R_g = 1.0$ | | 35 | 63 | ns | |
| Fall Time ^b | t _f | Ω | | 8 | 18 | | |
| Source-Drain Diode Ratings and Cha | aracteristics T | _C = 25 °C ^c | | | | | |
| Continuous Current | I _S | | | | 76 | Α | |
| Pulsed Current | I _{SM} | | | | 290 | A | |
| Forward Voltage ^a | V _{SD} | $I_F = 20 \text{ A}, V_{GS} = 0 \text{ V}$ | | 0.73 | 1.2 | V | |
| Reverse Recovery Time | t _{rr} | | | 22 | 62 | ns | |
| Peak Reverse Recovery Current | I _{RM} | I _F = 20 A, di/dt = 100 A/μs | | 1.4 | 3.9 | Α | |
| Reverse Recovery Charge | Q _{rr} | | | 0.019 | 0.134 | μC | |

- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%$
- b. Independent of operating temperature.
- c. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



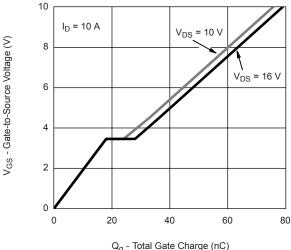
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



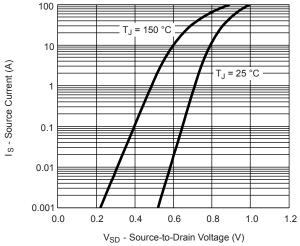


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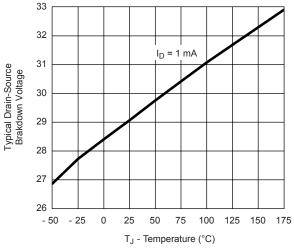
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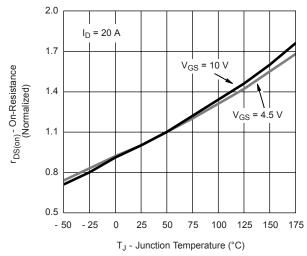




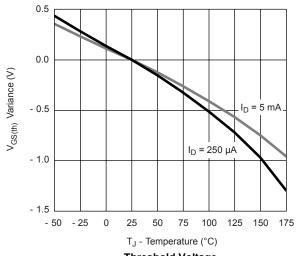
Source-Drain Diode Forward Voltage



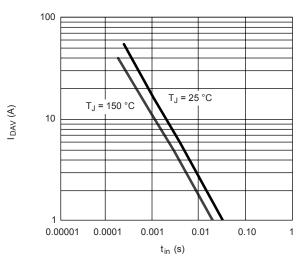
Typical Drain-Source Brakdown Voltage vs. Junction Temperature



On-Resistance vs. Junction Temperature



Threshold Voltage

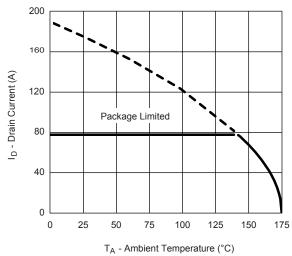


Single Pulse Avalanche Current vs. Time

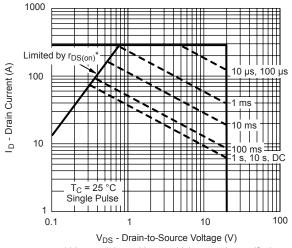


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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

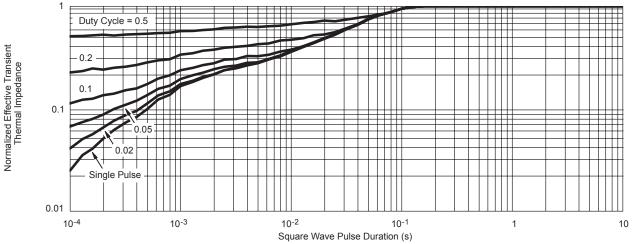


Drain Current vs. Ambient Temperature



* V_{GS} > minimum V_{GS} at which r_{DS(on)} is specified



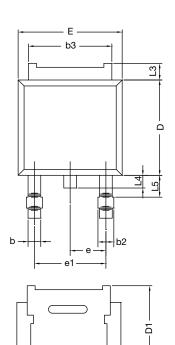


Normalized Thermal Transient Impedance, Junction-to-Case

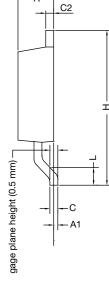




TO-252A CASE OUTLINE



E1



| | MILLIMETERS | | MILLIMETERS INCHES | | HES |
|---------------------------------|-------------|-------|--------------------|-------|-----|
| DIM. | MIN. | MAX. | MIN. | MAX. | |
| Α | 2.18 | 2.38 | 0.086 | 0.094 | |
| A1 | - | 0.127 | - | 0.005 | |
| b | 0.64 | 0.88 | 0.025 | 0.035 | |
| b2 | 0.76 | 1.14 | 0.030 | 0.045 | |
| b3 | 4.95 | 5.46 | 0.195 | 0.215 | |
| С | 0.46 | 0.61 | 0.018 | 0.024 | |
| C2 | 0.46 | 0.89 | 0.018 | 0.035 | |
| D | 5.97 | 6.22 | 0.235 | 0.245 | |
| D1 | 5.21 | - | 0.205 | - | |
| E | 6.35 | 6.73 | 0.250 | 0.265 | |
| E1 | 4.32 | - | 0.170 | - | |
| Н | 9.40 | 10.41 | 0.370 | 0.410 | |
| е | 2.28 | BSC | 0.090 BSC | | |
| e1 | 4.56 BSC | | 0.180 BSC | | |
| L | 1.40 | 1.78 | 0.055 | 0.070 | |
| L3 | 0.89 | 1.27 | 0.035 | 0.050 | |
| L4 | - | 1.02 | - | 0.040 | |
| L5 | 1.14 | 1.52 | 0.045 | 0.060 | |
| ECN: X12-0247-Rev. M. 24-Dec-12 | | | | | |

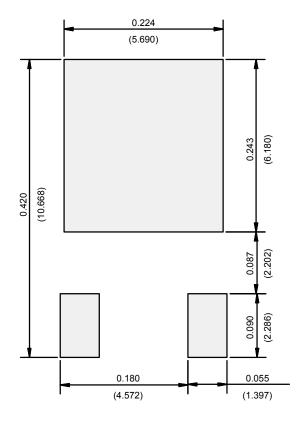
DWG: 5347

Note

• Dimension L3 is for reference only.



RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)



Recommended Minimum Pads Dimensions in Inches/(mm)

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